## ABSTRACT

## PROCESS FOR FABRICATING A STRUCTURE HAVING A BURIED DIELECTRIC LAYER OF UNIFORM THICKNESS

The invention relates to a process for fabricating a final structure (5) comprising in succession a useful semiconductor layer (3'), a dielectric layer (2) and a carrier substrate (4), the process comprising a step of providing an intermediate structure (1) including an upper layer (3), the dielectric layer (2) and the carrier substrate (4) and a step of finishing the intermediate structure (1) to form the final structure (5) comprising a treatment modifying nonuniformly the thickness of the dielectric layer (2) following a determined dissolution profile. According to the invention, the dielectric layer (2) of the intermediate structure (1) has a thickness profile complementary to the determined dissolution profile.


Figure 2